2SD669(A)

Rev.F Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

WR0459I ṂṂ Ł QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-126F Plastic Package.

/ Features

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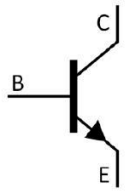
Complementary pair with 2SB649(A).

/ Applications

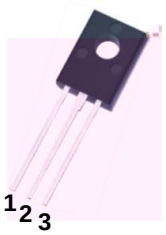
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Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



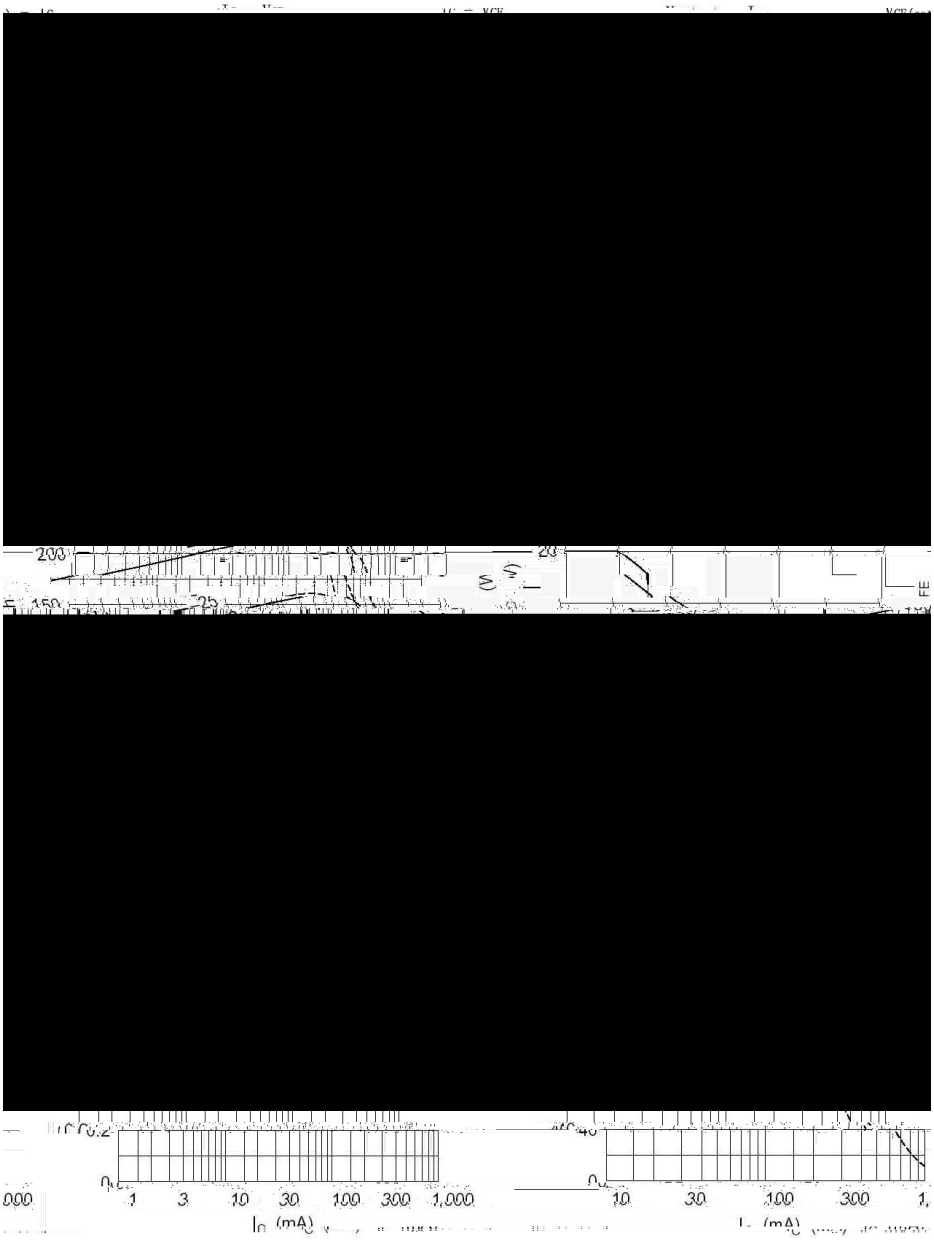
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

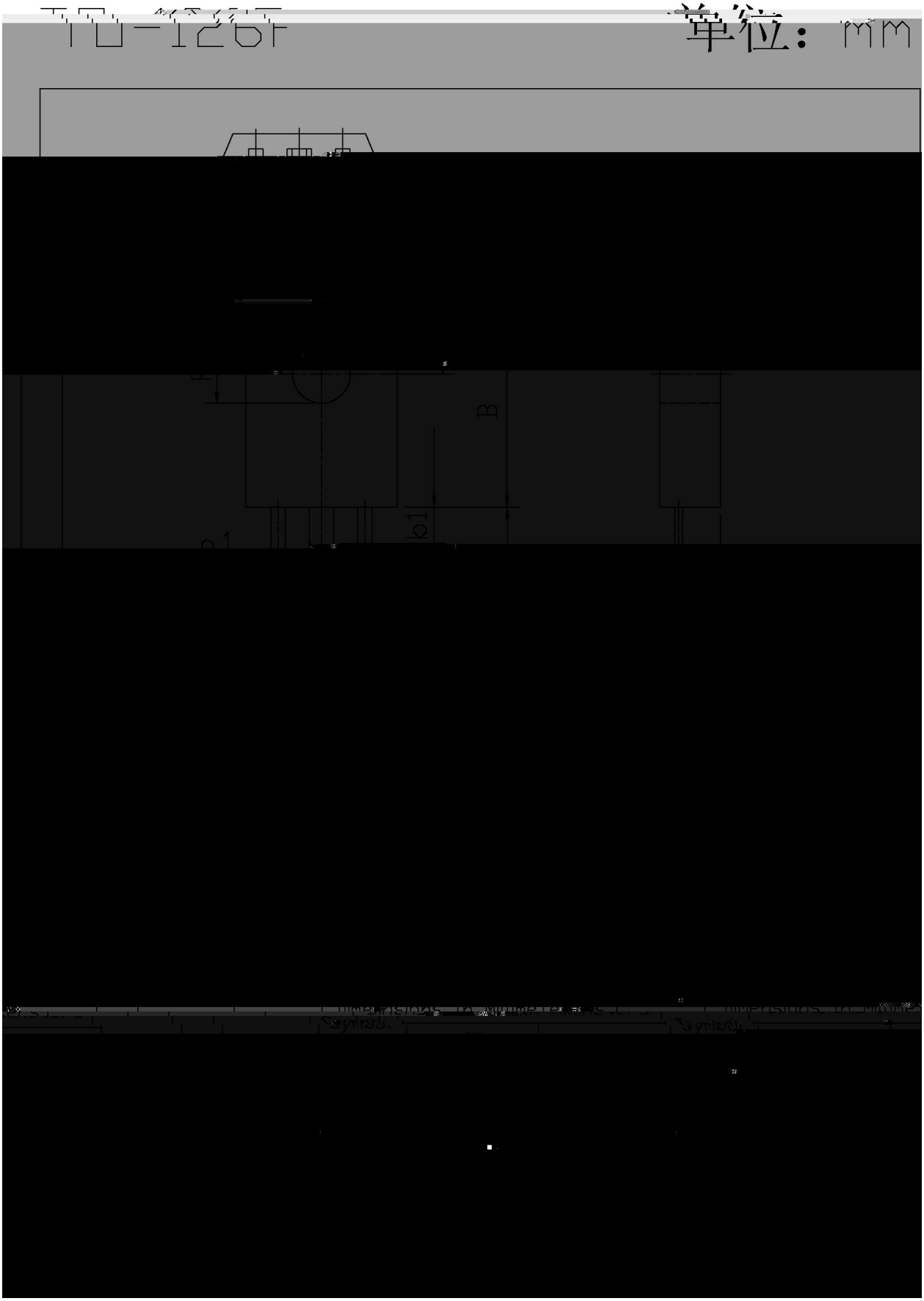
h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

v Ѭ Parameter	ϒ N Symbol	Ѭ Ө Rating	D Ң Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO} 2SD669	120	V 120

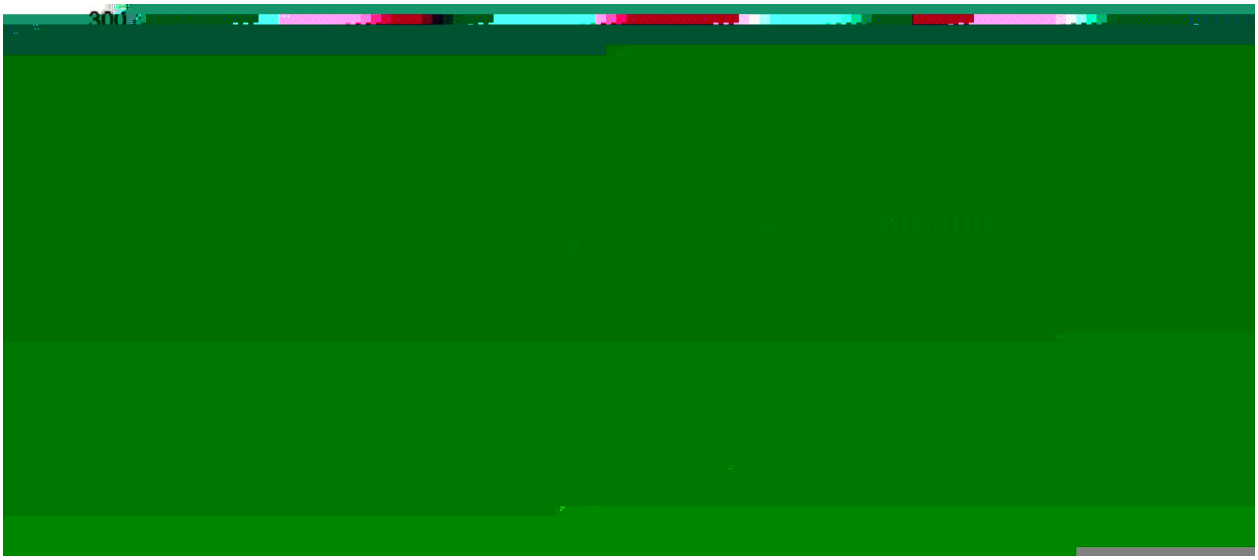
/ Electrical Characteristic Curve



/ Package Dimensions



( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ů 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ů 255 ° 5 ł ı `H ڑ `Y ٨ ѭ 5 ° 0.5sec;

3 ì ˙ ٩ ˛ ɔ ﻉ ů ѭ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

5	•	**ħu**	**q**	**ł**	˜	255 °